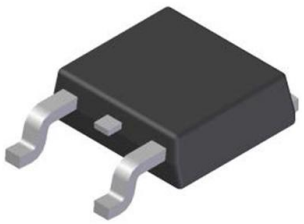
ZXMN10A11KTC Datasheet



DiGi Electronics Part Number	ZXMN10A11KTC-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	ZXMN10A11KTC
Description	MOSFET N-CH 100V 2.4A TO252-2
Detailed Description	N-Channel 100 V 2.4A (Ta) 2.11W (Ta) Surface Mount TO-252-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
ZXMN10A11KTC	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	2.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
6V, 10V	350mOhm @ 2.6A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 250µA	5.4 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	274 pF @ 50 V
FET Feature:	Power Dissipation (Max):
-	2.11W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-252-3	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
ZXMN10	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

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Lead-free Green

ZXMN10A11K

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = 25°C
100V	350mΩ @ V_{GS} = 10V	3.5A
	450mΩ @ V_{GS} = 6V	3.1A

Features and Benefits

- Fast switching speed
- Low input capacitance
- **"Green" Component and RoHS compliant (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

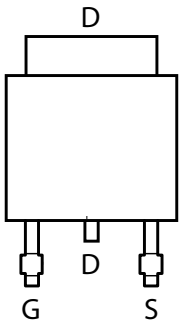
- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

Mechanical Data

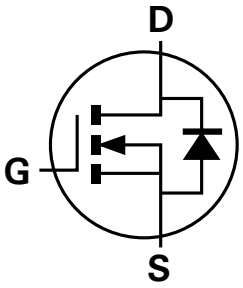
- Case: TO252-3L
- Case Material: Molded Plastic "Green" Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

TO252-3L

Top View



Pin Out – Top View



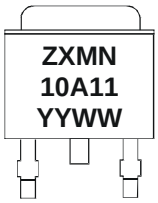
Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A11KTC	See Below	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMN = Product Type Marking Code, Line 1
10A11 = Product Type Marking Code, Line 2
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-52)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	100	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 3) T_A = 70°C (Note 3) (Note 2)	I_D	3.5 2.8 2.4	A
Pulsed Drain current	V_{GS} = 10V	(Note 4)	I_{DM}	9.9	A
Continuous Source current (Body diode)		(Note 3)	I_S	8.4	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	9.9	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	P_D	4.06 32.4	W mW/°C
	(Note 3)		8.5 68.0	
	(Note 6)		2.11 16.8	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	30.8	°C/W
	(Note 3)		14.7	
	(Note 6)		59.1	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{\theta JL}$	1.10	°C/W
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note 2, except the device is measured at t ≤ 10 sec.
4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
5. Thermal resistance from junction to solder-point (at the end of the drain lead).
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with the high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

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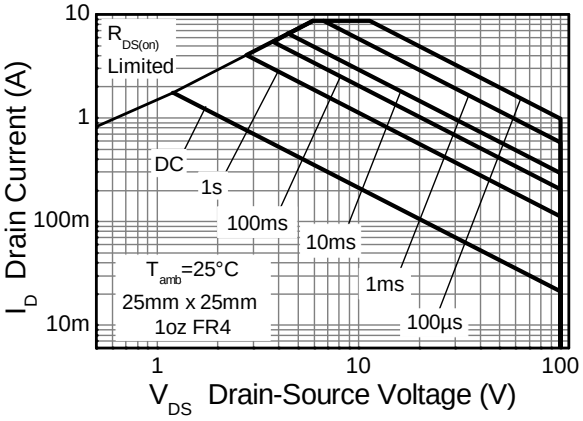
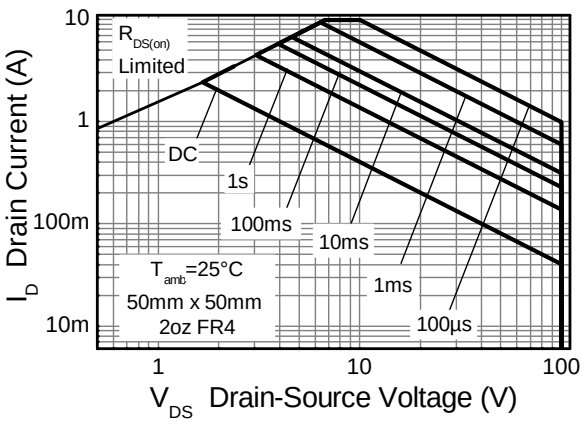
ZXMN10A11K

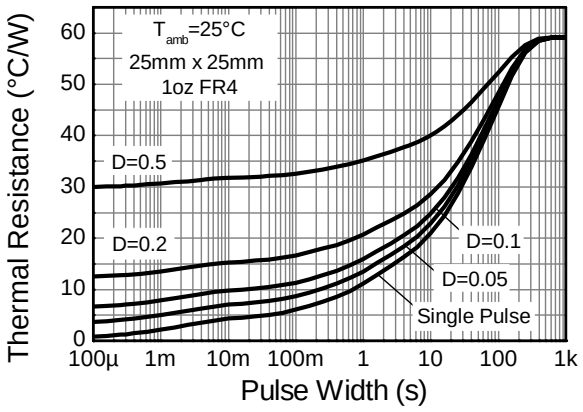
Thermal Characteristics



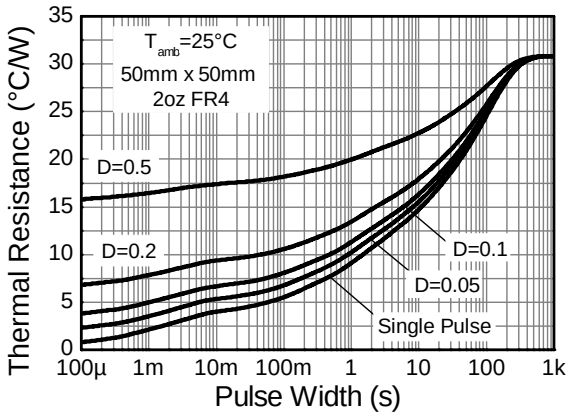
Safe Operating Area



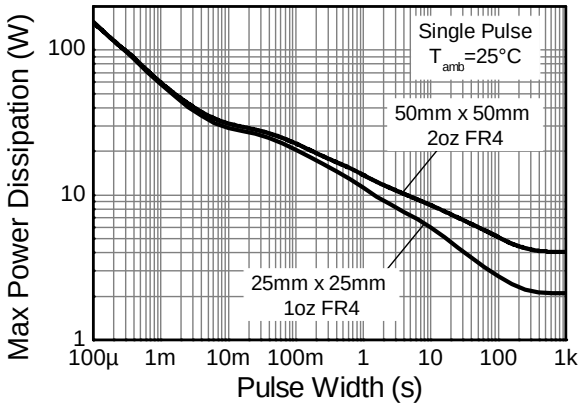
Safe Operating Area



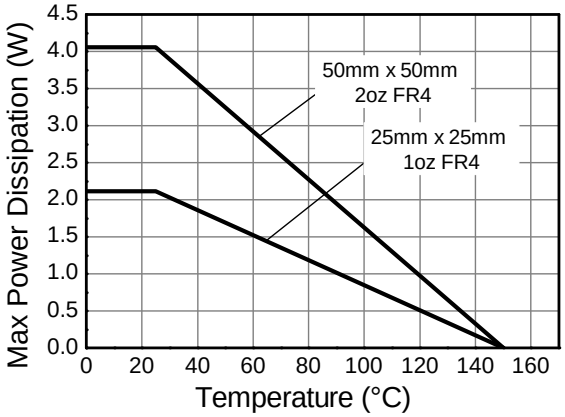
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	I_D = 250μA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	2	—	4	V	I_D = 250μA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 7)	$R_{DS\ (ON)}$	—	—	0.350	Ω	V_{GS} = 10V, I_D = 2.6A
				0.450		V_{GS} = 6V, I_D = 1.3A
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	4	—	S	V_{DS} = 15V, I_D = 2.6A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.850	0.950	V	I_S = 1.85A, V_{GS} = 0V
Reverse recovery time (Note 8)	t_{rr}	—	26	—	ns	I_S = 1.0A, di/dt = 100A/μs
Reverse recovery charge (Note 8)	Q_{rr}	—	30	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	274	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	21	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	11	—	pF	
Total Gate Charge (Note 9)	Q_g	—	3.5	—	nC	V_{GS} = 6V; V_{DS} = 50V, I_D = 2.5A
Total Gate Charge (Note 9)	Q_g	—	5.4	—	nC	V_{GS} = 10V; V_{DS} = 50V, I_D = 2.5A
Gate-Source Charge (Note 9)	Q_{gs}	—	1.4	—	nC	V_{GS} = 10V; V_{DS} = 50V, I_D = 2.5A
Gate-Drain Charge (Note 9)	Q_{gd}	—	1.5	—	nC	V_{GS} = 10V; V_{DS} = 50V, I_D = 2.5A
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	2.7	—	ns	V_{DD} = 50V, V_{GS} = 10V I_D = 1.0A, $R_G \cong 6\Omega$
Turn-On Rise Time (Note 9)	t_r	—	1.7	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	7.4	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	3.5	—	ns	

Notes: 7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperatures.

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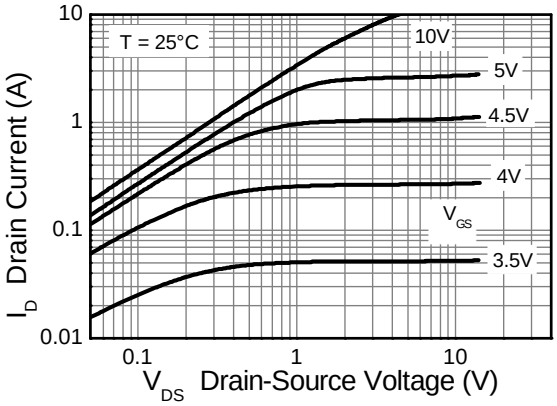
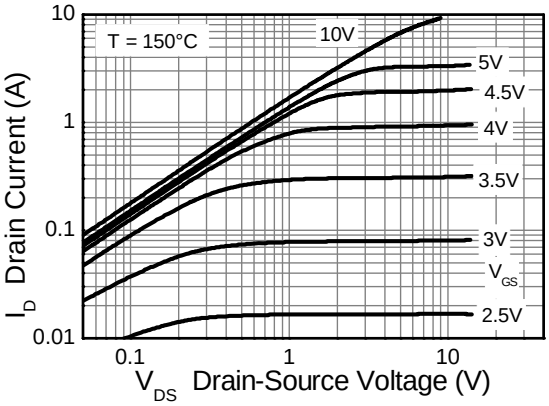
ZXMN10A11K

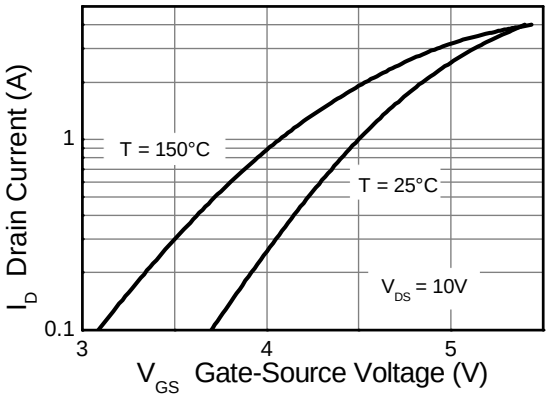
Typical Characteristics



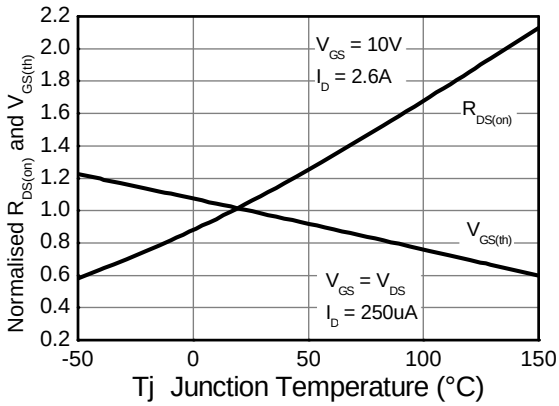
Output Characteristics



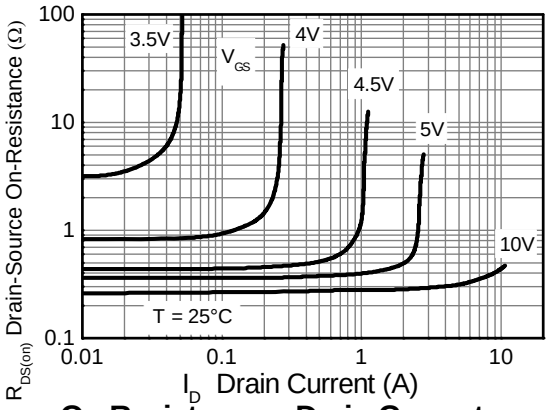
Output Characteristics



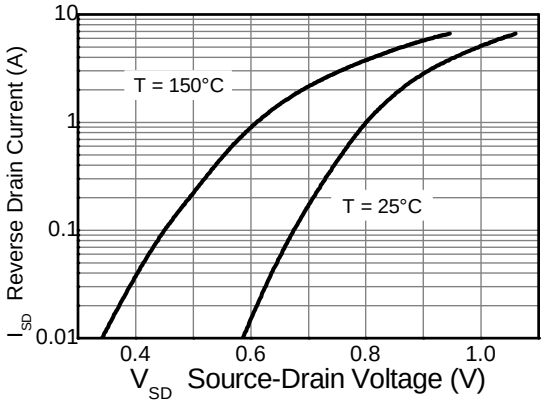
Typical Transfer Characteristics



Normalised Curves v Temperature



On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

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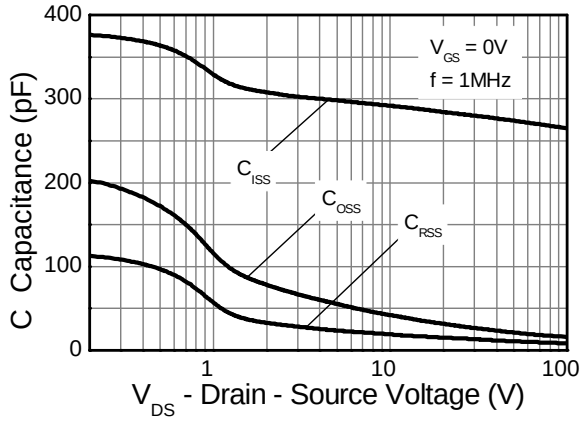
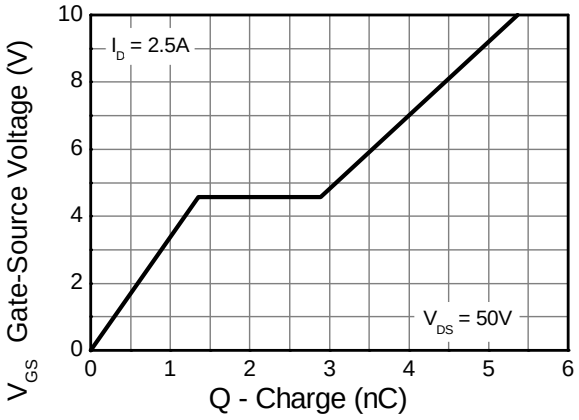
Typical Characteristics - continued

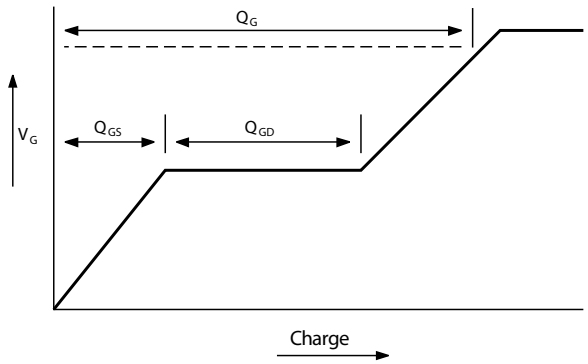


Capacitance v Drain-Source Voltage

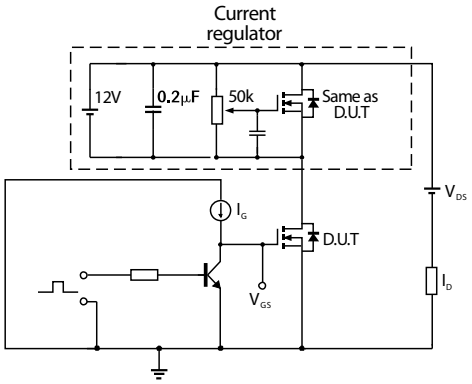


Gate-Source Voltage v Gate Charge

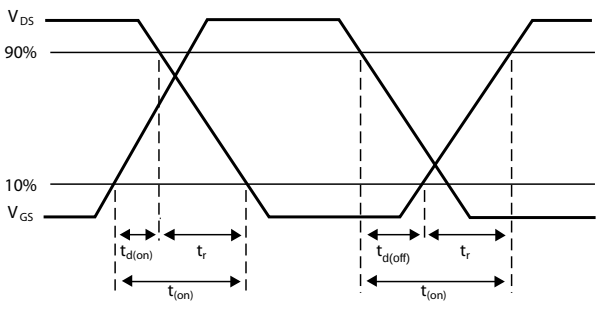
Test Circuits



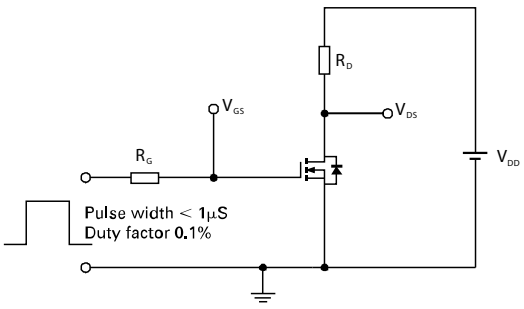
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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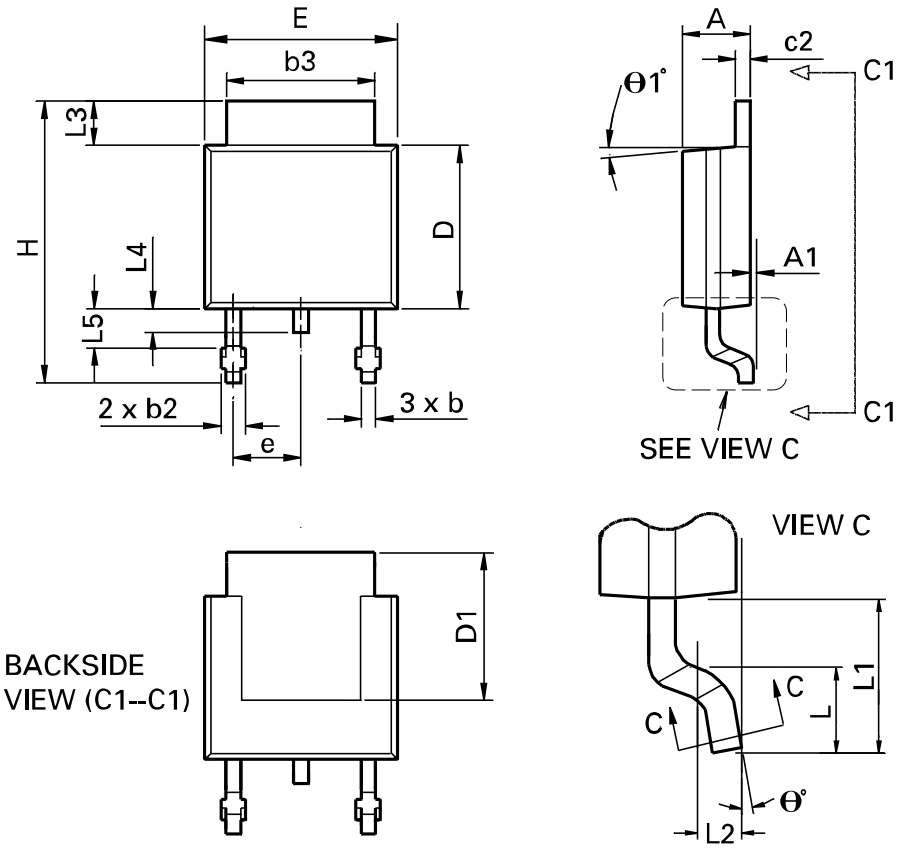
Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	**e**	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	**H**	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	**L**	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	**L1**	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	**L2**	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	**L3**	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	**L4**	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	**L5**	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	**θ1°**	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	**θ°**	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

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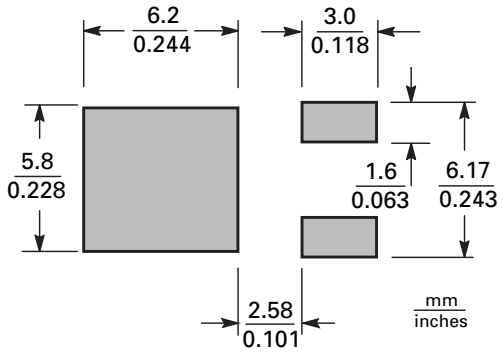
Suggested Pad Layout



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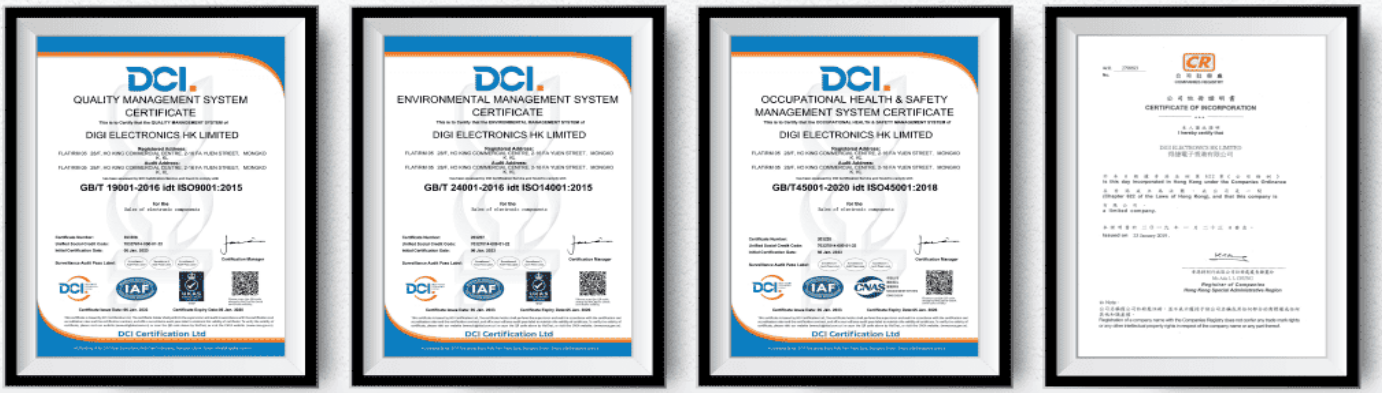

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